

# TLE4966V-1K

In Plane Sensing with Vertical Dual Hall Effect Latch  
for Automotive Applications

## Technical Product Description

Revision 1.1, 2013-09-23

**Edition 2013-09-23**

**Published by  
Infineon Technologies AG  
81726 Munich, Germany**

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## Revision History

| Page or Item | Subjects (major changes since previous revision) |
|--------------|--|
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### Revision 1.1, 2013-09-23

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| 15 | Parameter Bhys changed |
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## 1 Product Description



### 1.1 Target Applications

The TLE4966V-1K is specifically designed to detect the rotation direction and the rotation speed of a pole wheel. The sensing direction is **in-plane** to the sensor surface. Even at high distances to the hall elements the direction will be detected correctly.



Figure 1-1 Image of TLE4966V in the PG-TSOP6-6-5 package

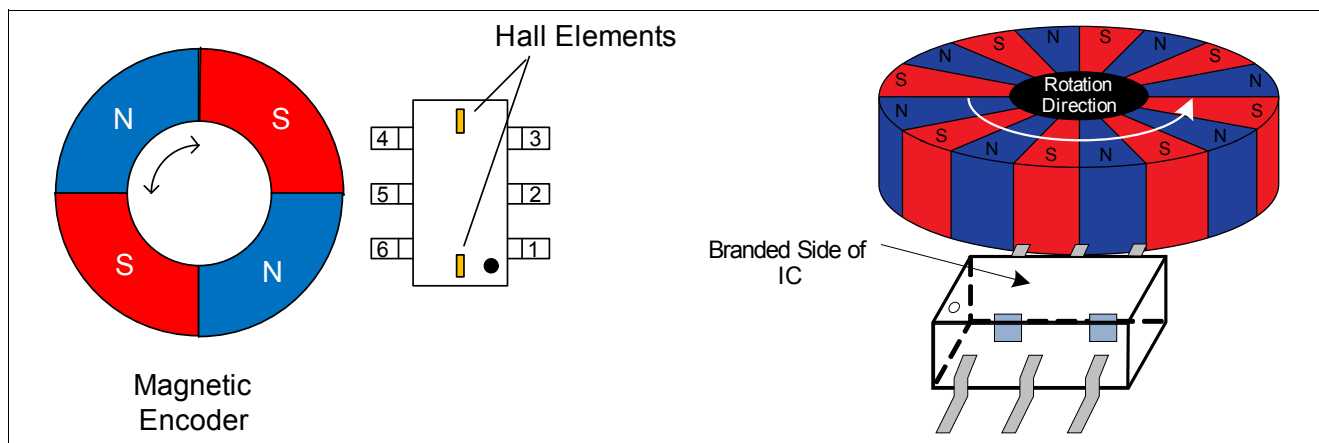


Figure 1-2 Target Application (top and side view): Sensing Direction parallel to target wheel

### 1.2 Features

- **In-Plane Sensing** for parallel mounting of magnetic encoder and sensor
- Low current consumption
- Direction Detection
- Speed output for index counting applications
- 3.5V to 32V operating supply voltage
- Operating from regulated power supply
- Reverse polarity protection (-18V)
- Over voltage capability up to 42 V without external resistor
- Output over current and over temperature protection
- High robustness to mechanical stress by Active Error Compensation
- Low drift of magnetic thresholds
- Low jitter (typ. 0.3us)
- SMD package PG-TSOP6-6-5

Table 1-1 Ordering Information

| Product Name | Product Type             | Ordering Code | Package   |
|--------------|--------------------------|---------------|-----------|
| TLE4966V     | Dual Vertical Hall Latch | SP001102894   | TSOP6-6-5 |

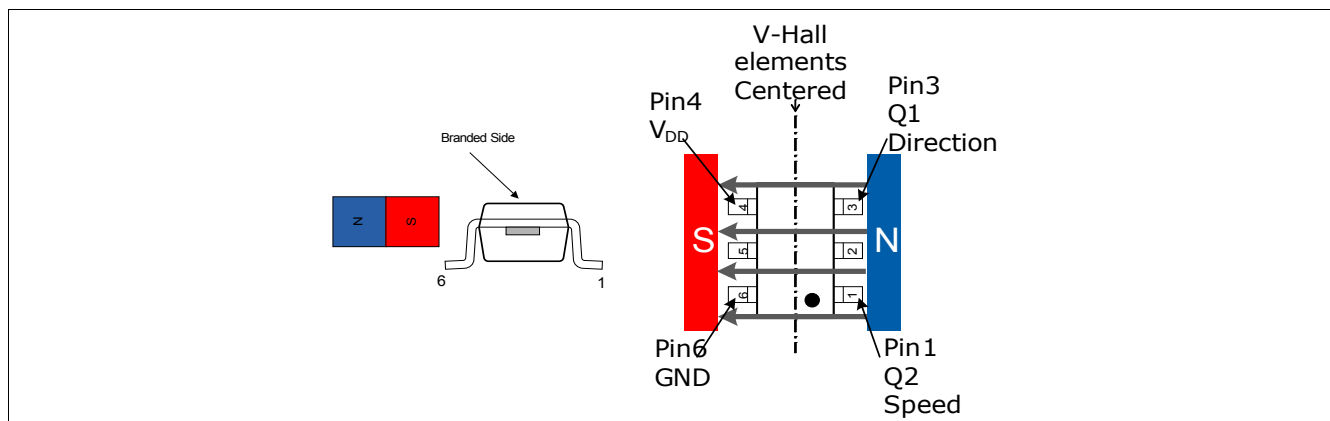
## 2 Functional Description

The TLE4966V-1K is specifically designed to detect the direction and rotational speed of a pole wheel as shown in [Figure 1-2](#).

### 2.1 General

The new Infineon Vertical Double Hall Switch TLE4966V-1K has integrated the functionality of detecting speed and direction of a rotating magnet, commonly known as pole wheel.

*Note: Completely new is the in plane field direction which will be detected with the TLE4966V-1K shown in [Figure 2-1](#) which enables completely new application layouts.*



**Figure 2-1 Target Application: Side view and top view for In-Plane Sensing**

The sensor provides a speed output at Q2 with the status (high or low) corresponding to the magnetic field value. For positive magnetic fields (south pole) exceeding the threshold  $B_{OP}$  the output is low, whereas for negative magnetic fields (north pole) lower than  $B_{RP}$  the output switches to high. The output Q1 can be either high or low depending on the direction of rotation of the pole wheel. This direction information is calculated internally. (see [Table 2-2](#))

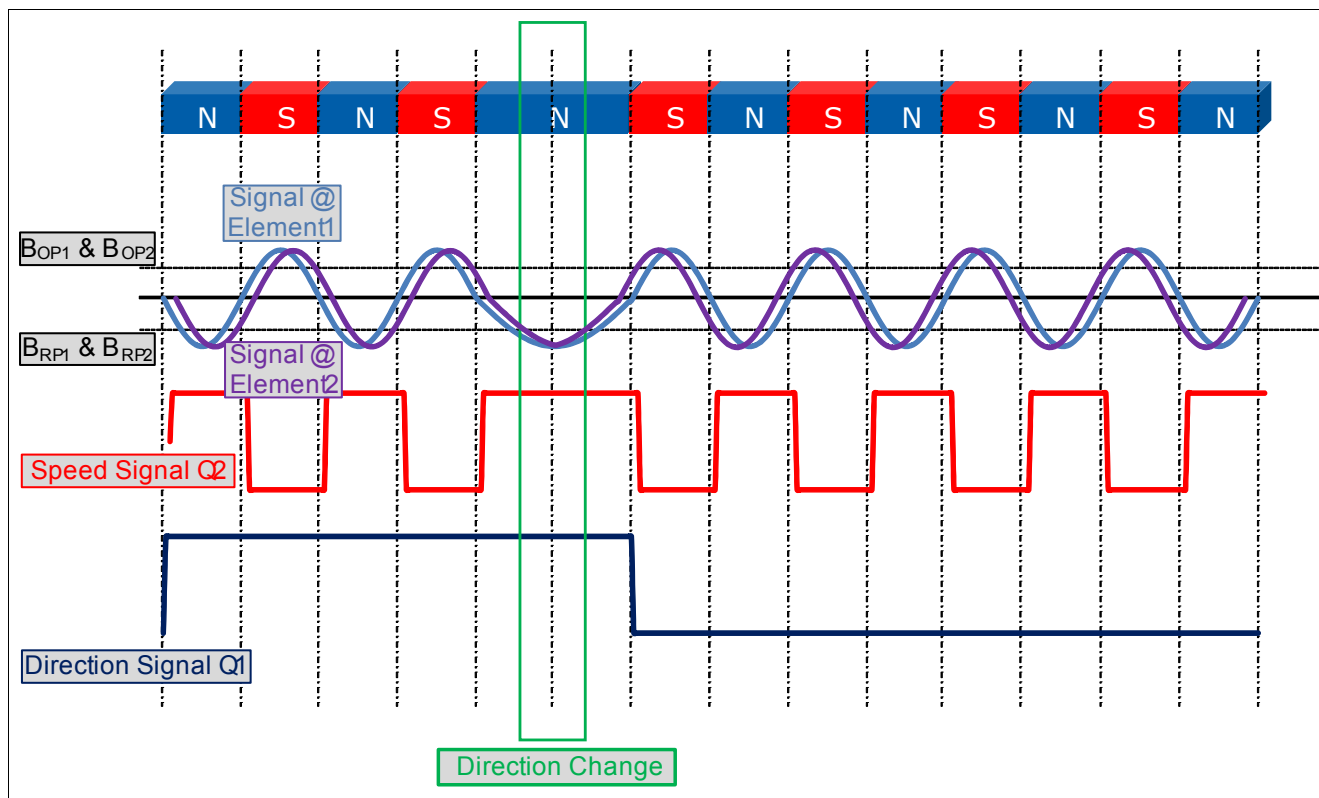
Designed in a new technology, this device offers high voltage capabilities with very small current consumption. The product can be operated from unregulated power supplies which offers our customers unique freedom of design for their system.

This product is AEC Q100 certified and enables our customers to build systems for the highest automotive quality requirements. The product has a TSOP6 package, which is RoHS compliant and fulfills the usual automotive environmental guidelines.

Application Examples are:

- Window lifter (index counting)
- Power closing (index counting)
- All applications with the need of speed and direction detection.

[Figure 2-2](#) and [Table 2-1](#) show the mapping of a pole wheel with the two corresponding output signals of the device.



**Figure 2-2** Magnetic field signal with the corresponding speed & direction output including the definition of the direction signal

**Table 2-1** Output Pin Q1 Direction Signals

| Rotation direction | State of direction output Q1 |
|--------------------|------------------------------|
| Counterclockwise   | Low                          |
| Clockwise          | High                         |



## 2.2 Pin Configuration (top view)

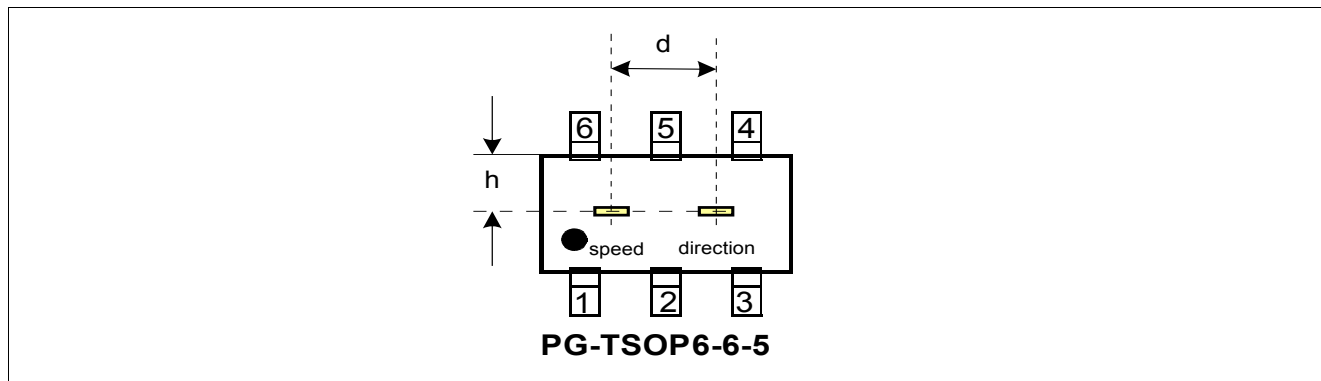


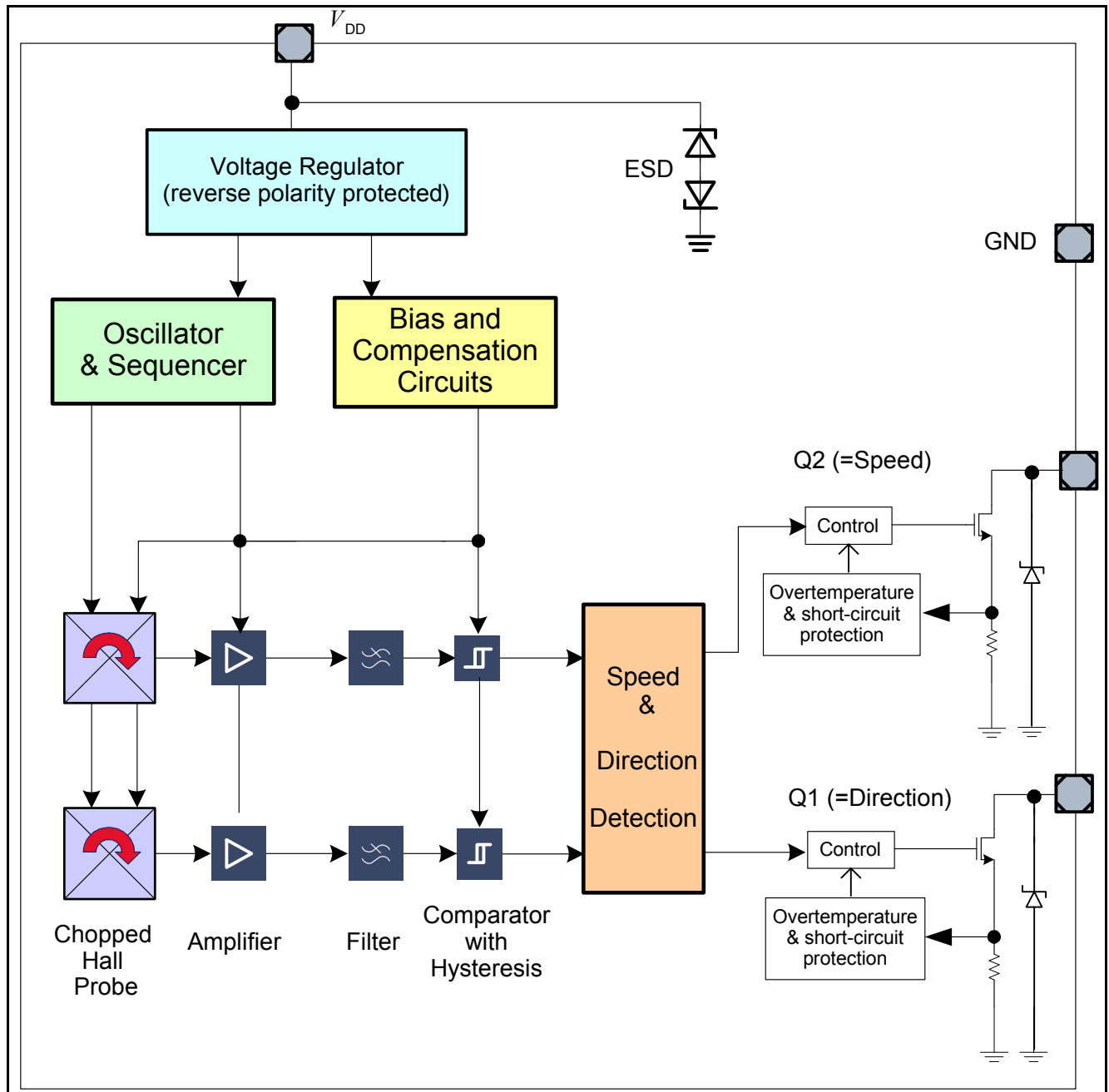
Figure 2-3 PG-TSOP6-6-5 Pin Configuration and sensitive area (d = 1.25mm) (see table 2-2)

Table 2-2 Pin Description PG-TSOP6-6-5

| Pin No. | Symbol   | Function                      |
|---------|----------|-------------------------------|
| 1       | Q2       | Speed                         |
| 2       | GND      | Recommended connection to GND |
| 3       | Q1       | Direction                     |
| 4       | $V_{DD}$ | Supply voltage                |
| 5       | GND      | Recommended connection to GND |
| 6       | GND      | Ground                        |



## 2.3 Block Diagram



**Figure 2-4 Functional Block Diagram of the TLE4966V-1K**

The chopped Dual Hall IC switch comprises a Hall probe, bias generator, compensation circuits, oscillator and output transistor.

The bias generator provides currents for the Hall probe and the active circuits. Compensation circuits stabilize the temperature behavior and reduce influence of technology variations.

The active error compensations (chopping technique) rejects offsets in the signal path. Therefore the influence of mechanical stress to the Hall elements caused by molding and soldering processes and other thermal stress in the package is minimized. The chopped measurement principle together with the threshold generator and the comparator ensures highly accurate and temperature stable magnetic thresholds. The output transistor has an integrated over current and over temperature protection to prevent the device from destruction.

## 2.4 Start-up Behavior

The magnetic threshold exhibit a hysteresis  $B_{\text{hys}} = B_{\text{op}} - B_{\text{rp}}$ . In case of a power-on with a magnetic field  $B$  within hysteresis ( $B_{\text{rp}} < B < B_{\text{op}}$ ) the output of the sensor is set to the pull up voltage level " $V_Q$ " per default. After the first crossing of  $B_{\text{op}}$  or  $B_{\text{rp}}$  of the magnetic field the internal decision logic is set to the corresponding magnetic input value.

$V_{\text{DDA}}$  is the internal supply voltage which is following the external supply voltage  $V_{\text{DD}}$ .

This means for  $B > B_{\text{op}}$  the output is switching for  $B > B_{\text{rp}}$  and  $B_{\text{op}} > B > B_{\text{rp}}$  the output stays at  $V_Q$

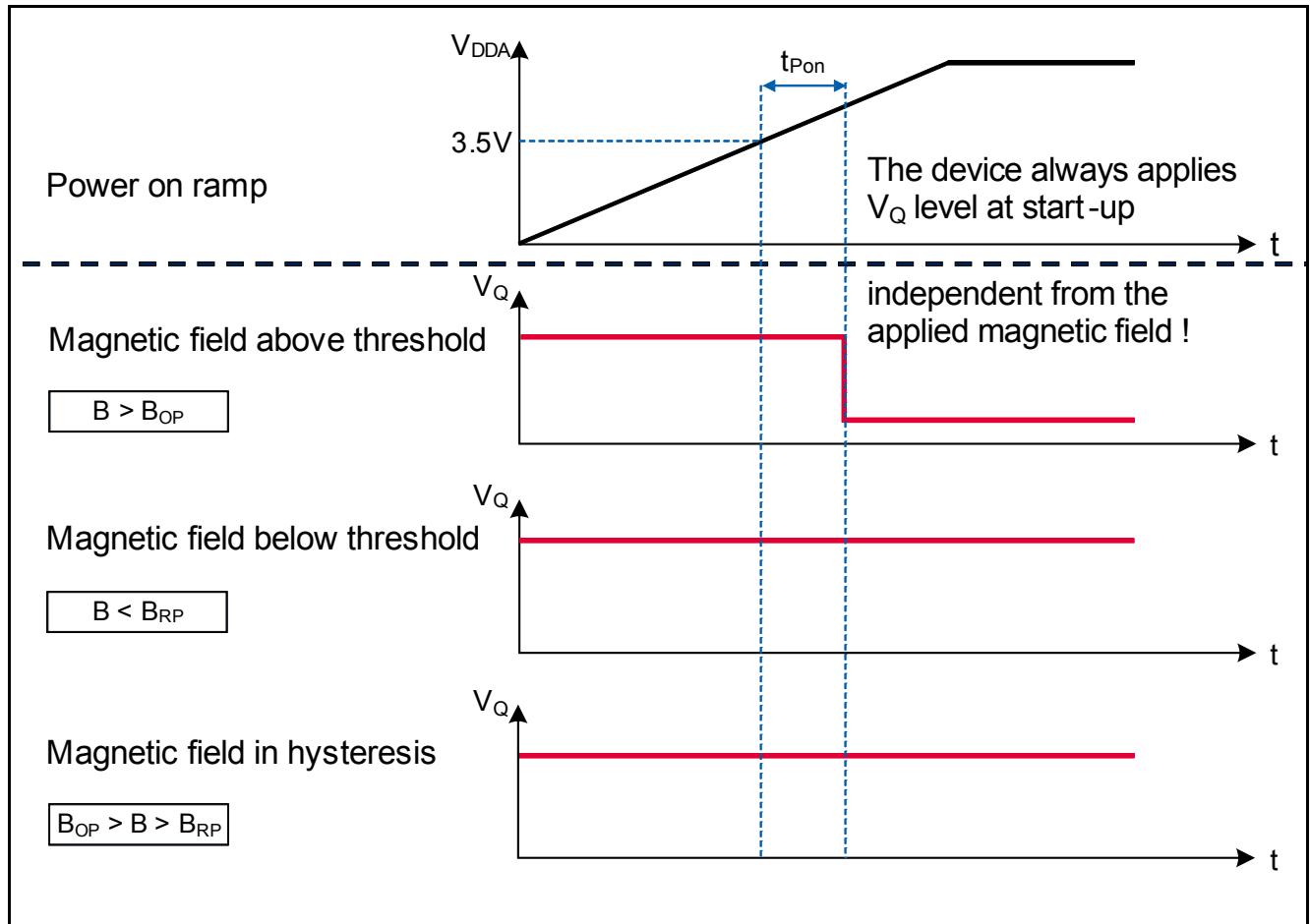


Figure 2-5 Start-up behavior of the at different magnetic start conditions

## 2.5 Application Circuit

The **Figure 2-6** below shows the basic option of an application circuit. The Resistor  $R_Q$  has to be in a dimension to match the applied  $V_S$  to keep  $I_Q$  limited to the operating range of maximal 10mA. For example:  $V_S = 12V$ ,  $I_Q < 10mA \rightarrow R = 12V / 0.01A = 1.2k\Omega \rightarrow R_Q > 1.2k\Omega$ .

In **Figure 2-7** additional ESD Diodes are optional the achieve an increased ESD robustness at the Q pins. Furthermore with the (optional) 47nF between  $V_{DD}$  and GND a high system level robustness is achieved.

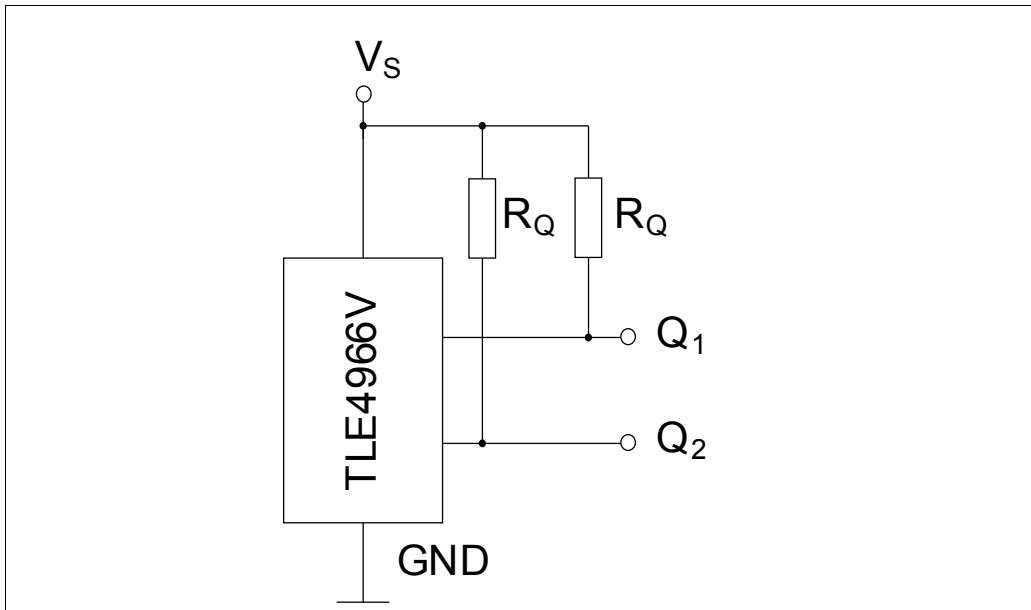


Figure 2-6 Basic Application Circuit

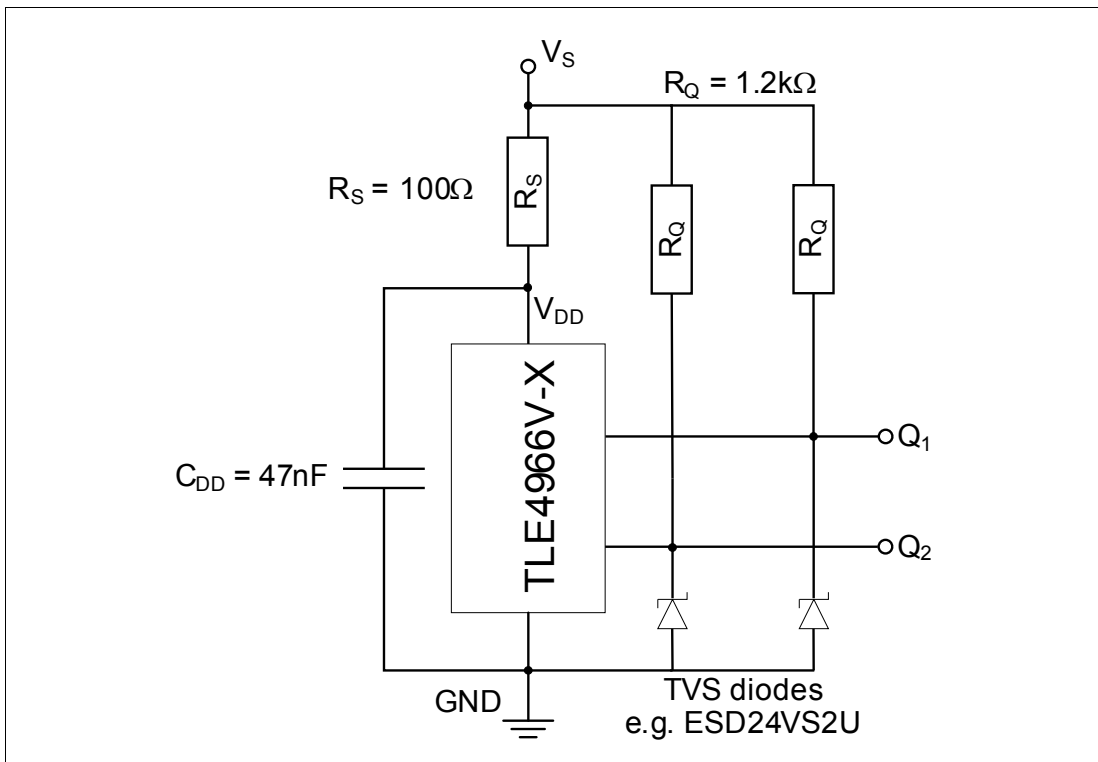


Figure 2-7 Enhanced Application Circuit for very high ESD robustness on system level

### 3 Specification

#### 3.1 Absolute Maximum Ratings

**Table 3-1 Absolute Maximum Rating Parameters**

| Parameter                              | Symbol     | Limit Values |                          | Unit | Note / Test Condition  |
|--|------------|--------------|--------------------------|------|--|
|  |            | Min.         | Max.                     |      |  |
| Supply voltage                         | $V_{DD}$   | -18          | 32<br>42                 | V    | 10h, no external resistor required   |
| Output voltage                         | $V_Q$      | -0.5         | 32                       | V    |  |
| Reverse output current                 | $I_Q$      | -35          |                          | mA   |  |
| Junction temperature                   | $T_J$      | -40          | 155<br>165<br>175<br>195 | °C   | for 2000h (not additive)<br>for 1000h (not additive)<br>for 168h (not additive)<br>for 3 x 1h (additive) |
| Storage temperature                    | $T_S$      | -40          | 150                      | °C   |  |
| Thermal resistance<br>Junction ambient | $R_{thJA}$ |              | 200                      | K/W  | for PG-TSOP6-6-5   |
| Thermal resistance<br>Junction lead    | $R_{thJL}$ |              | 100                      | K/W  | for PG-TSOP6-6-5   |

**Attention: Stresses above the max. values listed here may cause permanent damage to the device.**  
**Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.**

Calculation of the dissipated power  $P_{DIS}$  and junction temperature  $T_J$  of the chip in TSOP6:

e.g for:  $V_{DD} = 12\text{ V}$ ,  $I_S = 10\text{ mA}$ ,  $V_{QSAT} = 0.5\text{ V}$ ,  $I_Q = 10\text{ mA}$

Power dissipation:  $P_{DIS} = 12\text{ V} \times 10\text{ mA} + 2 \times (0.5\text{ V} \times 10\text{ mA}) = 120\text{ mW} + 10\text{ mW} = 130\text{ mW}$

Temperature  $\Delta T = R_{thJA} \times P_{DIS} = 200\text{ K/W} \times 130\text{ mW} = 26\text{ K}$

For  $T_A = 100^\circ\text{C}$ :  $T_J = T_A + \Delta T = 100^\circ\text{C} + 26\text{ K} = 126^\circ\text{C}$

**Table 3-2 ESD Protection<sup>1)</sup> ( $T_A = 25^\circ\text{C}$ )**

| Parameter                       | Symbol    | Limit Values |      | Unit | Note / Test Condition                          |
|---------------------------------|-----------|--------------|------|------|--|
|                                 |           | Min.         | Max. |      |  |
| ESD voltage (HBM) <sup>2)</sup> | $V_{ESD}$ | -2           | +2   | kV   | $R = 1.5\text{ k}\Omega$ , $C = 100\text{ pF}$ |
| System level test               |           | -6           | +6   |      | Figure 2.7 <sup>3)</sup>                       |

1) Characterization of ESD is carried out on a sample basis.

2) Human Body Model (HBM) tests according to EIA/JESD22-A114

3) Gun test (2k $\Omega$ /330pF or 330 $\Omega$ /150pF) according to ISO 10605-2008

### 3.2 Operating Range

**Attention:** The following operating conditions must not be exceeded in order to ensure correct operation of the TLE4966V-1K. All parameters specified in the following sections refer to these operating conditions unless otherwise mentioned.

**Table 3-3 Operating Conditions Parameters**

| Parameter                                     | Symbol    | Values |      |                  | Unit | Note / Test Condition |
|---|-----------|--------|------|------------------|------|-----------------------|
|   |           | Min.   | Typ. | Max.             |      |                       |
| Supply voltage                                | $V_{DD}$  | 3.5    |      | 32 <sup>1)</sup> | V    |                       |
| Output voltage                                | $V_Q$     | -0.3   |      | 32               | V    |                       |
| Junction temperature                          | $T_j$     | -40    |      | 150              | °C   |                       |
| Output current                                | $I_Q$     | 0      |      | 10               | mA   |                       |
| Magnetic signal input frequency <sup>2)</sup> | $f_{mag}$ | 0      |      | 5                | kHz  |                       |

1) Latch-up test with factor 1.5 is not covered. Please see max ratings also.

2) For operation at the maximum switching frequency the magnetic input signal must be 1.4 times higher than for static fields. This is due to the -3dB corner frequency of the internal low-pass filter in the signal path.

### 3.3 Electrical Characteristics

**Table 3-4 General Electrical Characteristics**

| Parameter  | Symbol       | Values |      |      | Unit          | Note / Test Condition   |
|--|--------------|--------|------|------|---------------|---|
|  |              | Min.   | Typ. | Max. |               |   |
| Supply current   | $I_S$        | 3.9    | 5.8  | 7.3  | mA            |   |
| Reverse current  | $I_{SR}$     | -      | 0.05 | 1    | mA            | for $V_{DD} = -18V$   |
| Output saturation voltage  | $V_{QSAT}$   | -      | 0.2  | 0.5  | V             | $I_Q = 10mA$  |
| Output leakage current   | $I_{QLEAK}$  | -      | -    | 5.0  | $\mu A$       | $T=150^\circ C$ , 12V   |
| Output current limitation  | $I_{QLIMIT}$ | 20     | 30   | 40   | mA            | internally limited & thermal shutdown                                       |
| Output fall time <sup>1)</sup>   | $t_f$        | 0.1    | 0.2  | 1    | $\mu s$       | 1.2k $\Omega^2$ / 50pF, see <a href="#">Figure 4-1</a>                      |
| Output rise time <sup>1)</sup>   | $t_r$        | 0.1    | 0.2  | 1    | $\mu s$       | 1.2k $\Omega^2$ / 50pF, see <a href="#">Figure 4-1</a>                      |
| Output jitter <sup>3)1)</sup>  | $t_{QJ}$     |        | 0.3  | 1    | $\mu s$       | For square wave signal with 1kHz  |
| Effective noise value of the magnetic switching points <sup>4)1)</sup> | $B_{Neff}$   |        | 45   |      | $\mu T_{RMS}$ |   |
| Delay time <sup>5)1)</sup>   | $t_d$        | 8      | 20   | 30   | $\mu s$       | see <a href="#">Figure 4-1</a>  |
| Signal Count Delay <sup>1)</sup>                                       | $t_{dc}$     | 50     | 400  | 1000 | ns            | 1.2k $\Omega$ /50pF @ $V_Q=12V$ , Direction before Speed Signal, 50% to 50% |
| Power-on time <sup>6)1)</sup>  | $t_{PON}$    | 48     | 84   | 120  | $\mu s$       | $V_{DD} = 3.5 V$ , $B \leq B_{RP} - 0.5 mT$ or $B \geq B_{OP} + 0.5 mT$     |
| Chopper frequency <sup>1)</sup>  | $f_{OSC}$    |        | 1300 |      | kHz           |   |

1) Not subject to production test, verified by design/characterization

2) Current limitation has to be taken into consideration for  $V_S > 12V$  in order not to exceed 10mA

3) Output jitter is the  $1\sigma$  value of the output switching distribution.

4) The magnetic noise is normal distributed and can be assumed as nearly independent to frequency without sampling noise or digital noise effects. The typical value represents a the rms-value and corresponds therefore to a  $1\sigma$  probability of normal distribution. Consequently a  $3\sigma$  value corresponds to 0.3% probability of appearance.

5) Systematic delay between magnetic threshold reached and output switching.

6) Time from applying  $V_{DD} = 3.0 V$  to the sensor until the output is valid.

### 3.4 Magnetic Characteristics

**Table 3-5 Magnetic Characteristics**

| Parameter                              | Symbol             | T (°C) | Values |       |      | Unit  | Note / Test Condition                           |
|--|--------------------|--------|--------|-------|------|-------|---|
|  |                    |        | Min.   | Typ.  | Max. |       |   |
| Operating point                        | B <sub>OP</sub>    | -40    | 1.1    | 2.8   | 4.5  | mT    |   |
|  |                    | 25     | 0.9    | 2.5   | 4.1  |       |   |
|  |                    | 150    | 0.4    | 1.9   | 3.3  |       |   |
| Release point                          | B <sub>RP</sub>    | -40    | -4.5   | -2.8  | -1.1 | mT    |   |
|  |                    | 25     | -4.1   | -2.5  | -0.9 |       |   |
|  |                    | 150    | -3.3   | -1.9  | -0.4 |       |   |
| Hysteresis                             | B <sub>Hys</sub>   | -40    | 3.6    | 5.3   | 7.4  | mT    |   |
|  |                    | 25     | 3.4    | 5.0   | 6.8  |       |   |
|  |                    | 150    | 2.5    | 3.7   | 5.2  |       |   |
| Magnetic Matching                      | B <sub>Match</sub> |        | -1.0   |       | +1.0 | mT    | for (Bop1 - Bop2) and (Brp1 - Brp2); -40..125°C |
|  |                    |        | -1.5   |       | +1.5 |       | -40..150°C                                      |
| Magnetic Offset                        | B <sub>Off</sub>   |        | -1.0   |       | +1.0 | mT    | (Bop + Brp) / 2; -40..125°C                     |
|  |                    |        | -1.5   |       | +1.5 | mt    | (Bop + Brp) / 2; -40..150°C                     |
| Temperature Compensation <sup>1)</sup> | TC                 |        |        | -1700 |      | ppm/K | ferrite magnet                                  |

1) Not subject to production test, verified by design/characterization



## 4 Timing Diagrams for the Speed and Direction Output

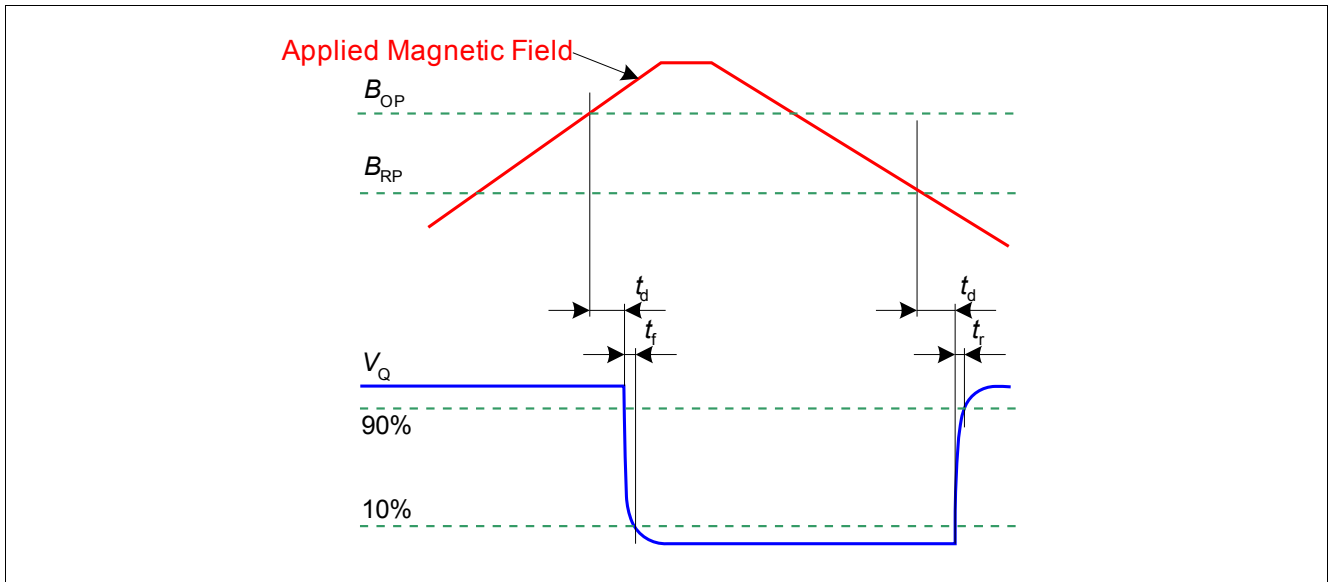


Figure 4-1 Timing Diagram TLE4966V

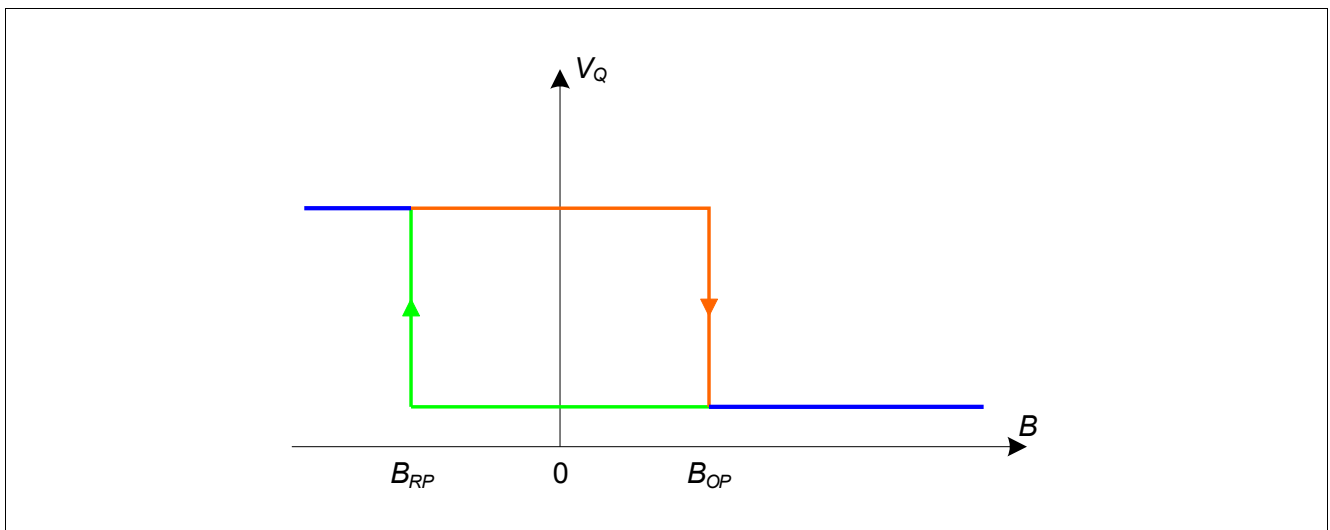
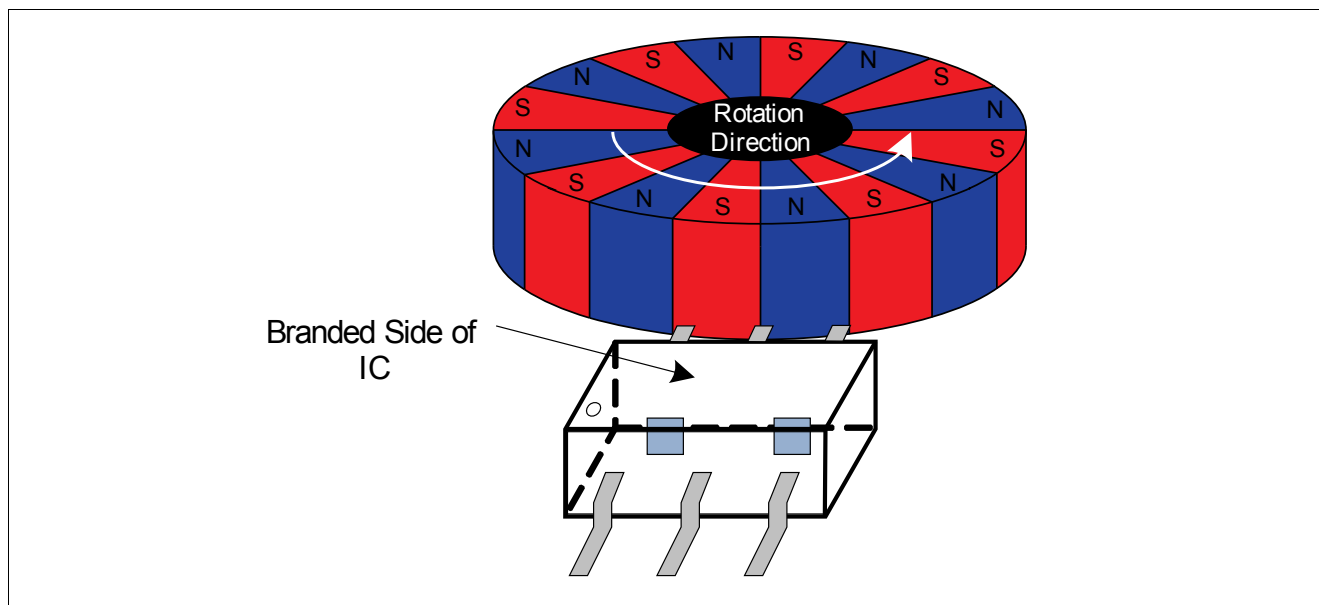


Figure 4-2 TLE4966V - Output Voltage Signal over applied magnetic Field

## Timing Diagrams for the Speed and Direction Output



**Figure 4-3 TLE4966V - Definition of the direction signal**

**Table 4-1 Output Pin Q1 Direction Signals**

| Rotation direction | State of direction output Q1 |
|--------------------|------------------------------|
| Counterclockwise   | Low                          |
| Clockwise          | High                         |

## 5 Package Information

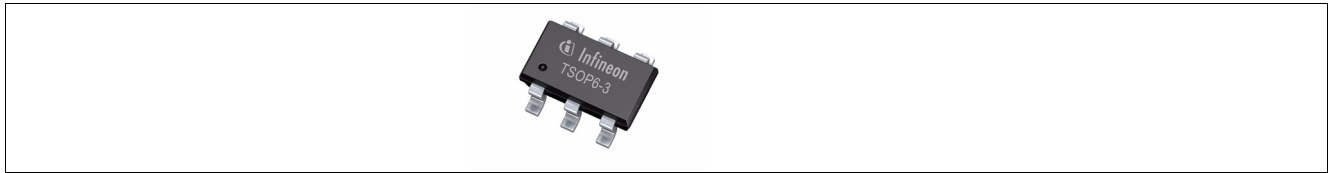


Figure 5-1 Image of TLE4966V in the PG-TSOP6-6-5 package

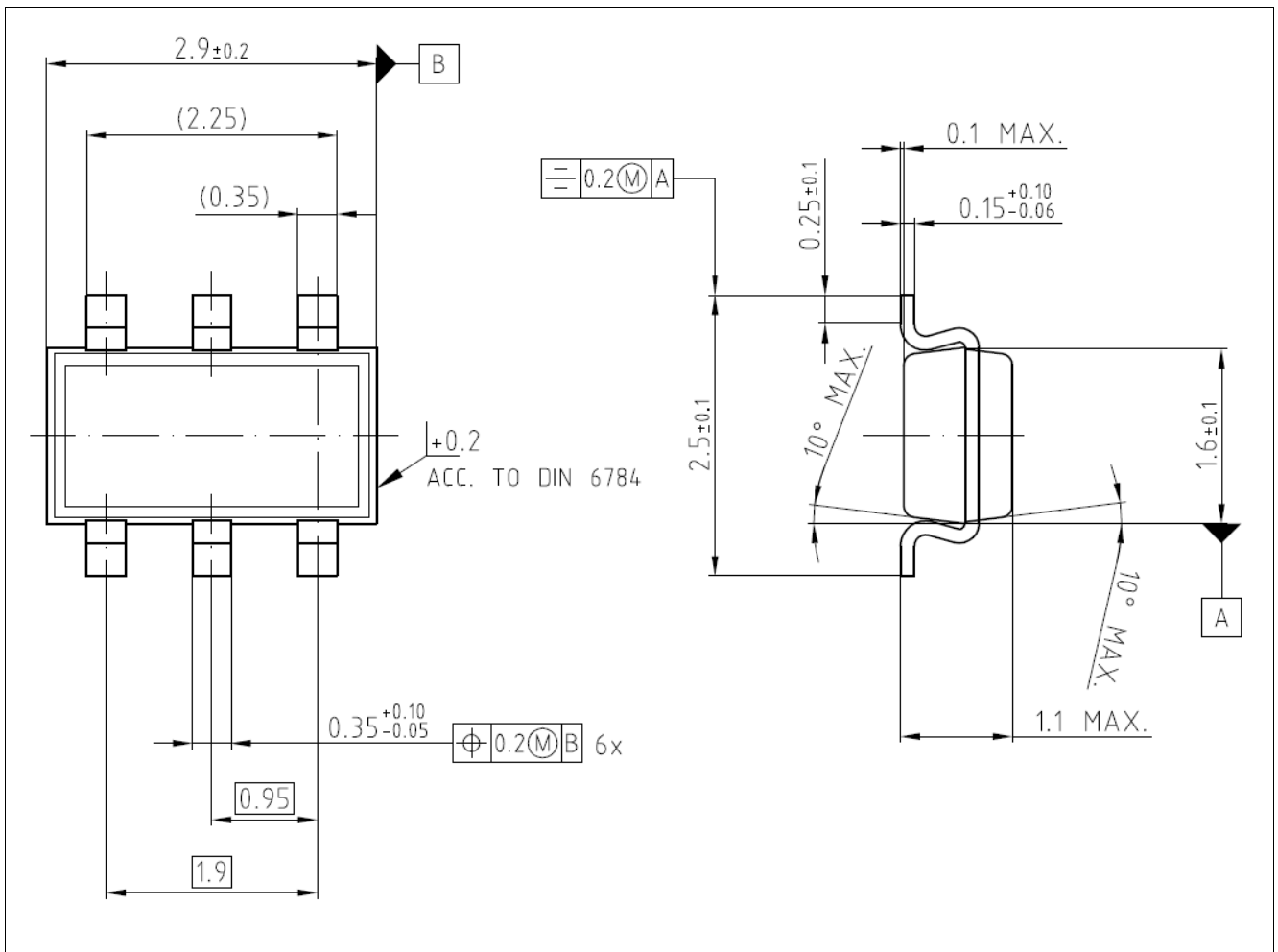
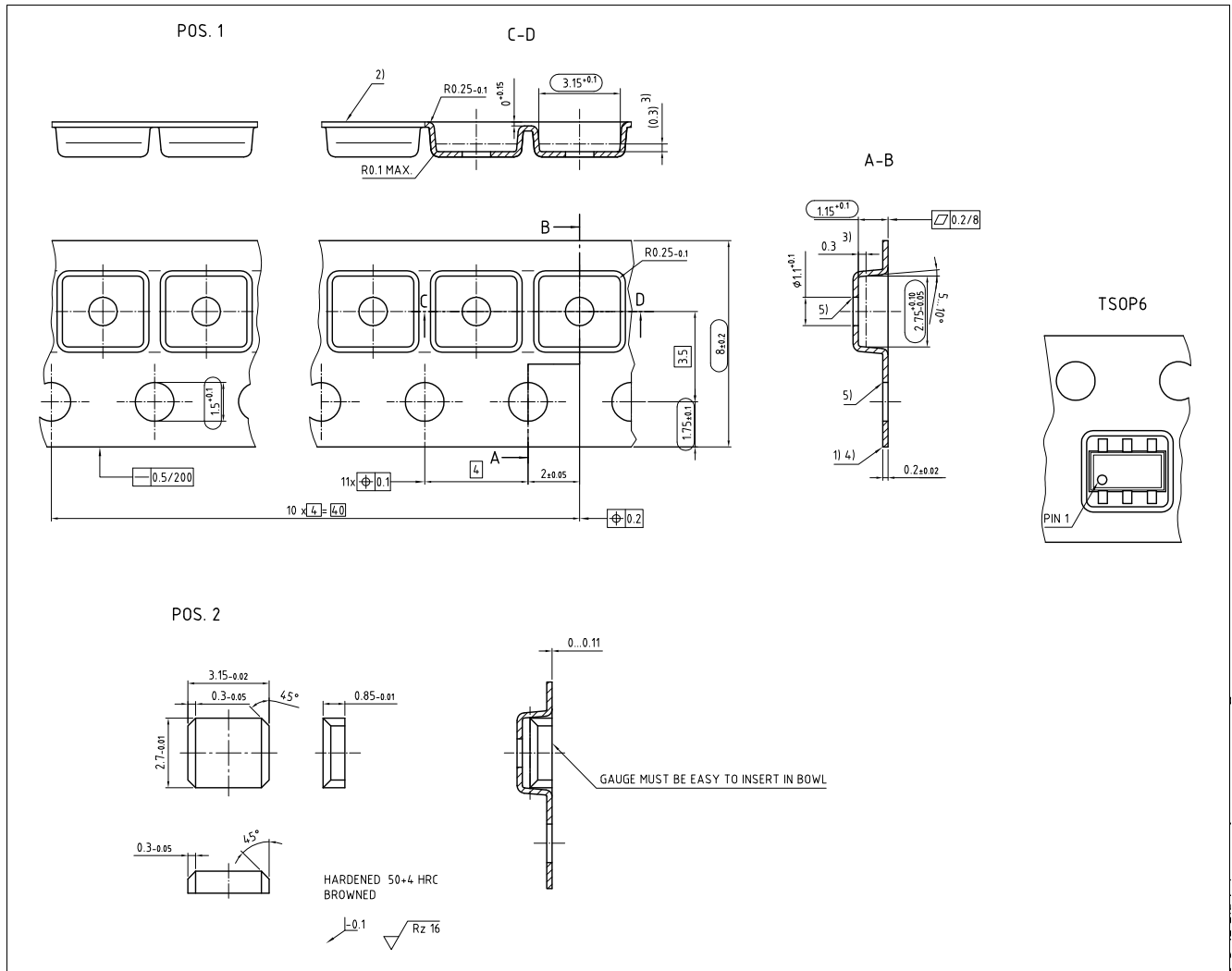
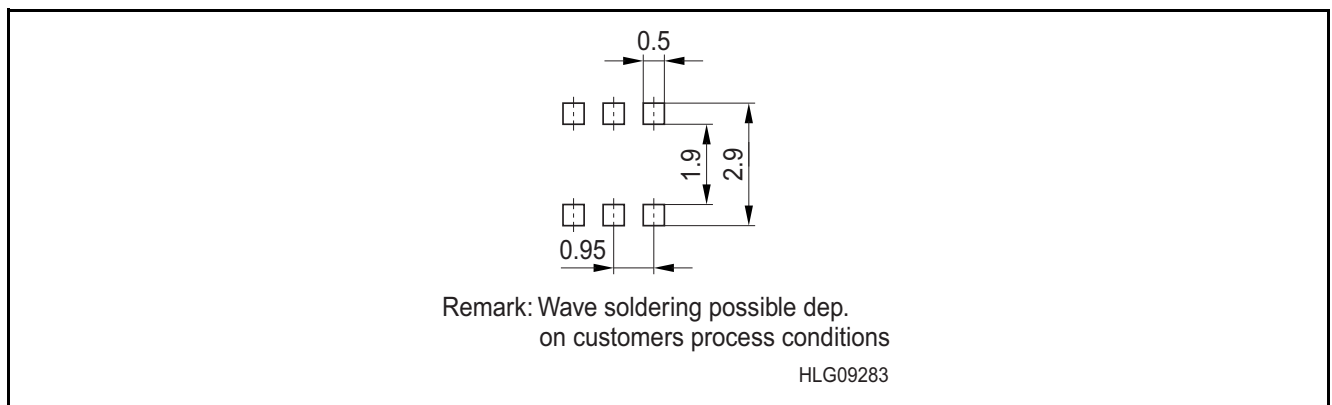


Figure 5-2 PG-TSOP6-6-5 Package Outline (All dimensions in mm)



**Figure 5-3 PG-TSOP6-6-5 Packing** (All dimensions in mm)

The sensitive elements are placed in an optimized distance (d) to guarantee the direction detection. To compensate package stress the sensitive elements are placed in the middle of the package (h).



**Figure 5-4 Footprint of PG-TSOP-6-6-5**

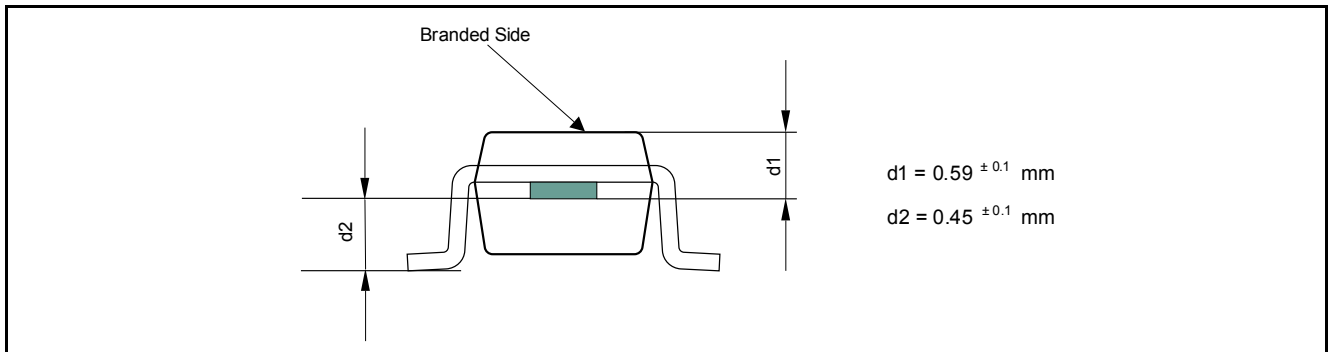


Figure 5-5 Distance between chip and package

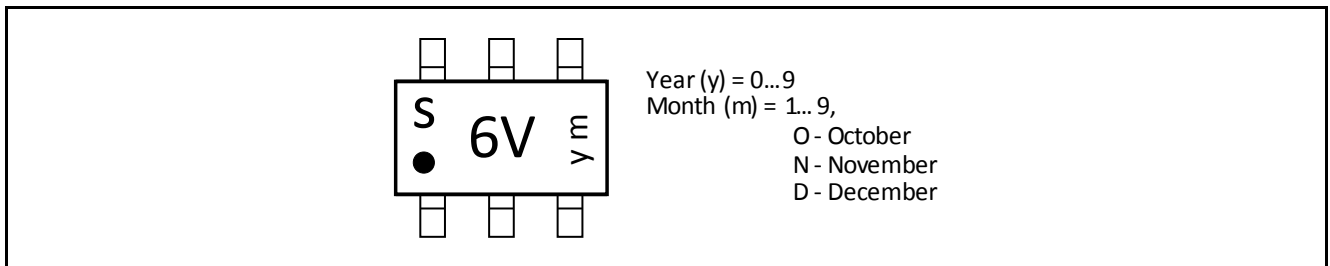


Figure 5-6 Marking of TLE4966V-1K

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